

U.S. Patent Application Serial No. 10/628,188
Fechko et al.
Amendment and Response (Office Action of 10/18/2005)
February 20, 2006
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Amendments to the Specification

Please replace original Paragraph 1 with the following amended

Paragraph 1:

[0001] The invention herein relates to controlling the nitrogen content in silicon carbide crystals and in particular relates to reducing the incorporation of nitrogen during sublimation growth of silicon carbide. This application is related to copending application Serial No. [_____] 10/628,189, filed concurrently herewith for "Growth of Ultra-High Purity Silicon Carbide Crystals in an Ambient Containing Hydrogen."